

Notice of References Cited	Application/Control No. 10/025,331	Applicant(s)/Patent Under Reexamination BOUCHARD ET AL.	
	Examiner Bao Q Truong	Art Unit 2187	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,430,527 B1	08-2002	Waters et al.	703/3
	B	US-6,308,219 B1	10-2001	Hughes, John H.	709/238
	C	US-4,912,698	03-1990	Bitzinger et al.	370/244
	D	US-4,766,535	08-1988	Auerbach et al.	711/165
	E	US-6,636,445 B2	10-2003	Ohshima et al.	365/190
	F	US-6,108,243 A	08-2000	Suzuki et al.	365/189.01
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Davis et al., The New DRAM Interfaces: SDRAM, DRDRAM and Variants, Oct. 2000, High Performance Computing, 3 rd ed. Int Symp.
	V	Sato et al., Fast Cycle RAM (FCRAM); a 20-ns Random Row Access, Pipe-Lined Operating DRAM, 1998, Symp. on VLSI Circuits Digest of Technical Papers.
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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